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ISL9V2040D3S / ISL9V2040S3S / ISL9V2040P3

EcoSPARK[®] 200mJ, 400V, N-Channel Ignition IGBT

General Description

The ISL9V2040D3S, ISL9V2040S3S, and ISL9V2040P3 are the next generation ignition IGBTs that offer outstanding SCIS capability in the space saving D-Pak (TO-252), as well as the industry standard D²-Pak (TO-263) and TO-220 plastic packages. This device is intended for use in automotive ignition circuits, specifically as a coil driver. Internal diodes provide voltage clamping without the need for external components.

EcoSPARK¤ devices can be custom made to specific clamp voltages. Contact your nearest Fairchild sales office for more information.

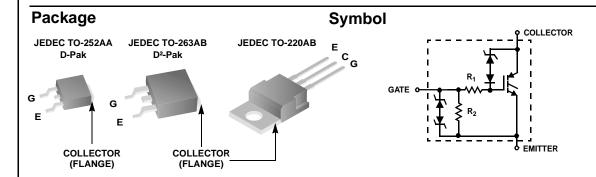
Formerly Developmental Type 49444

Applications

- · Automotive Ignition Coil Driver Circuits
- Coil- On Plug Applications

Features

- Space saving D Pak package available
- SCIS Energy = 200mJ at T_J = 25°C
- Logic Level Gate Drive



Device Maximum Ratings T_A = 25°C unless otherwise noted

Symbol	Parameter	Ratings	Units
BV _{CER}	Collector to Emitter Breakdown Voltage (I _C = 1 mA)	430	V
BV _{ECS}	Emitter to Collector Voltage - Reverse Battery Condition (I _C = 10 mA)	24	V
E _{SCIS25}	At Starting $T_J = 25$ °C, $I_{SCIS} = 11.5$ A, $L = 3.0$ mHy	200	mJ
E _{SCIS150}	At Starting $T_J = 150$ °C, $I_{SCIS} = 8.9$ A, $L = 3.0$ mHy	120	mJ
I _{C25}	Collector Current Continuous, At T _C = 25°C, See Fig 9	10	Α
I _{C110}	Collector Current Continuous, At T _C = 110°C, See Fig 9	10	Α
V _{GEM}	Gate to Emitter Voltage Continuous	±10	V
P _D	Power Dissipation Total T _C = 25°C	130	W
	Power Dissipation Derating T _C > 25°C	0.87	W/°C
T _J	Operating Junction Temperature Range	-40 to 175	°C
T _{STG}	Storage Junction Temperature Range	-40 to 175	°C
TL	Max Lead Temp for Soldering (Leads at 1.6mm from Case for 10s)	300	°C
T _{pkg}	Max Lead Temp for Soldering (Package Body for 10s)	260	°C
ESD	Electrostatic Discharge Voltage at 100pF, 1500Ω	4	kV

Device Marking		Device Pa		ackage Reel Size		Tape Width		Qı	Quantity	
V2040D		ISL9V2040D3ST	TC)-252AA	330mm	16mm		:	2500	
V2040S		ISL9V2040S3ST		-263AB	330mm	24mm			800	
V2040P		ISL9V2040P3	TC)-220AB	Tube	N/A			50	
V2040D		ISL9V2040D3S		-252AA	Tube	N/A			75	
V204	_	ISL9V2040S3S	<u>. </u>)-263AB	Tube		N/A		50	
Symbol	ai Char	Parameter	5°C un	•	noted	Min	Тур	Max	Unit	
ff State	Characte	eristics		I			, ,,			
BV _{CER}	Collector to Emitter Breakdown Voltage			$I_C = 2mA$, $V_{GE} = 0$, $R_G = 1K\Omega$, See Fig. 15 $T_{\perp} = -40$ to 150°C		370	400	430	V	
BV _{CES}	Collector	collector to Emitter Breakdown Voltage		$I_C = 10$ mA, $V_{GE} = 0$, $R_G = 0$, See Fig. 15 $T_J = -40$ to 150°C		390	420	450	V	
BV _{ECS}	Emitter to	Collector Breakdown V	oltage	$I_C = -75 \text{mA}, V$ $T_C = 25 ^{\circ}\text{C}$	$I_C = -75 \text{mA}, V_{GE} = 0 \text{V},$		-	-	V	
BV_GES	Gate to E	Emitter Breakdown Voltage		$I_{GES} = \pm 2mA$		±12	±14	-	V	
I _{CER}	Collector	to Emitter Leakage Curr	ent	$V_{CER} = 250V$		-	-	25	μA	
				$R_G = 1KΩ$, See Fig. 11	T _C = 150°C	-	-	1	mA	
I _{ECS}	Emitter to	Collector Leakage Curr	ent	V _{EC} = 24V, Se		-	-	1	mA	
				Fig. 11	$T_C = 150$ °C	-	-	40	mA	
R ₁		Series Gate Resistance				-	70	-	Ω	
R ₂		Emitter Resistance				10K	-	26K	Ω	
V _{CE(SAT)}	Characteristics Collector to Emitter Saturation Voltage		I _C = 6A,	T _C = 25°C,	-	1.45	1.9	V		
				$V_{GE} = 4V$	See Fig. 3					
V _{CE(SAT)}	Collector to Emitter Saturation Voltage			$I_{C} = 10A,$ $V_{GE} = 4.5V$	T _C = 150°C See Fig. 4	-	1.95	2.3	V	
ynamic (Charact	eristics								
Q _{G(ON)}	Gate Charge		I _C = 10A, V _{CE} = 12V, V _{GE} = 5V, See Fig. 14		-	12	-	nC		
V _{GE(TH)}	Gate to E	mitter Threshold Voltage	Э	$I_{C} = 1.0 \text{mA},$		1.3	-	2.2	V	
				V _{CE} = V _{GE} , See Fig. 10	T _C = 150°C	0.75	-	1.8	V	
V_{GEP}	Gate to E	Emitter Plateau Voltage		$I_C = 10A, V_{CE}$	= 12V	-	3.4	-	V	
witching	Charac	teristics								
t _{d(ON)R}	Current 7	Turn-On Delay Time-Res	istive	$V_{CE} = 14V, R_{L} = 1\Omega,$		-	0.61	-	μs	
t _{riseR}	Current F	Rise Time-Resistive		$V_{GE} = 5V, R_G = 1K\Omega$ $T_J = 25$ °C		-	2.17	-	μs	
t _{d(OFF)L}	Current	Turn-Off Delay Time-Indu	ıctive	$V_{CE} = 300V, L = 500\mu Hy,$ $V_{GE} = 5V, R_G = 1K\Omega$ $T_J = 25^{\circ}C, See Fig. 12$		-	3.64	-	μs	
t _{fL}	Current F	Fall Time-Inductive				-	2.36	-	μs	
SCIS	Self Clan	nped Inductive Switching	1	$T_J = 25^{\circ}\text{C}$, L = 3.0mHy, R _G = 1K Ω , V _{GE} = 5V, See Fig. 1 & 2		-	-	200	mJ	
hermal C	haracte	eristics								
$R_{\theta JC}$	Thermal	Resistance Junction-Cas	se	TO-252, TO-2	-	-	1.15	°C/\		

Typical Performance Curves

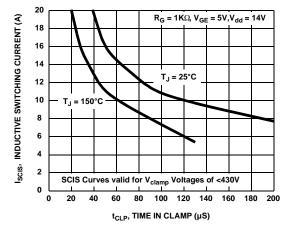


Figure 1. Self Clamped Inductive Switching Current vs Time in Clamp

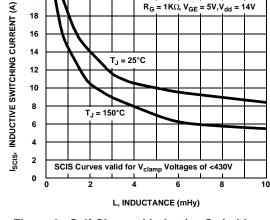


Figure 2. Self Clamped Inductive Switching Current vs Inductance

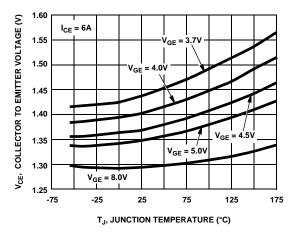


Figure 3. Collector to Emitter On-State Voltage vs Junction Temperature

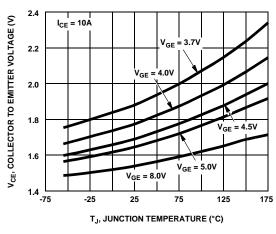


Figure 4. Collector to Emitter On-State Voltage vs Junction Temperature

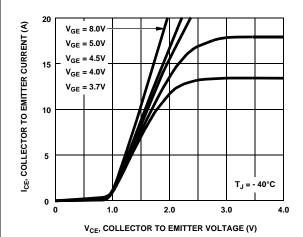


Figure 5. Collector to Emitter On-State Voltage vs Collector Current

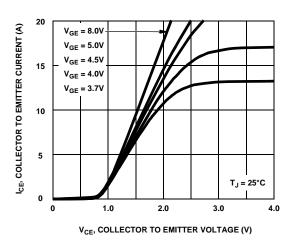
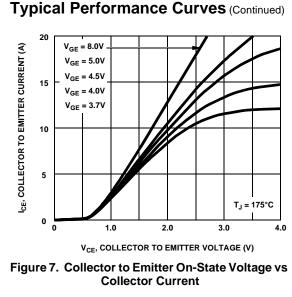


Figure 6. Collector to Emitter On-State Voltage vs Collector Current



DUTY CYCLE < 0.5%, V_{CE} = 5V
PULSE DURATION = 250µs

25

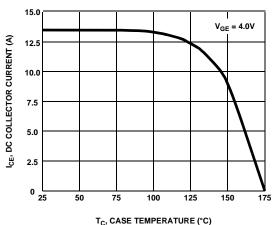
T_J = 150°C

T_J = 25°C

T_J = 40°C

V_{GE}, GATE TO EMITTER VOLTAGE (V)

Figure 8. Transfer Characteristics



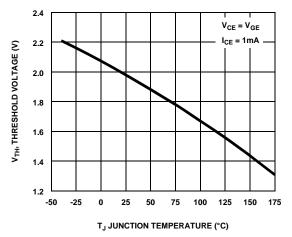
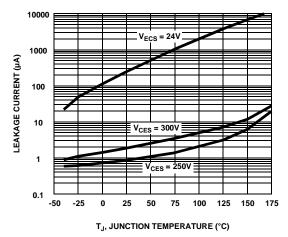


Figure 9. DC Collector Current vs Case Temperature

Figure 10. Threshold Voltage vs Junction Temperature



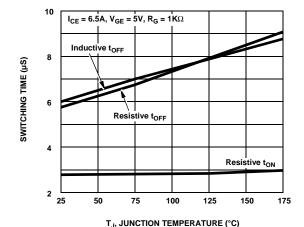
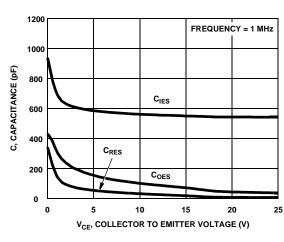


Figure 11. Leakage Current vs Junction Temperature

Figure 12. Switching Time vs Junction Temperature



Typical Performance Curves (Continued)

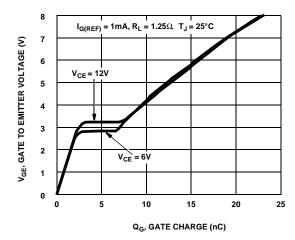


Figure 13. Capacitance vs" Collector to Emitter Voltage

Figure 14. Gate Charge

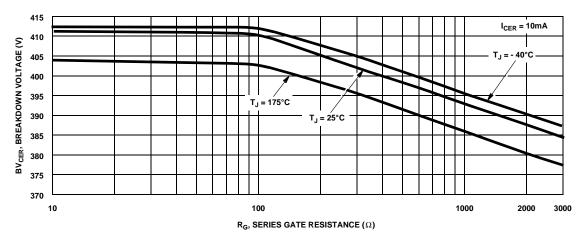


Figure 15. Breakdown Voltage vs "Series Gate Resistance

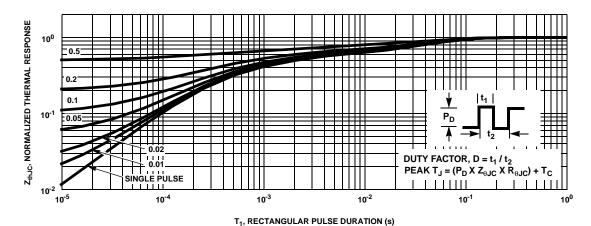
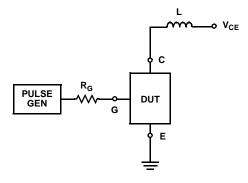


Figure 16. IGBT Normalized Transient Thermal Impedance, Junction to Case

Test Circuit and Waveforms



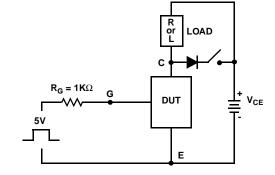


Figure 17. Inductive Switching Test Circuit

Figure 18. t_{ON} and t_{OFF} Switching Test Circuit

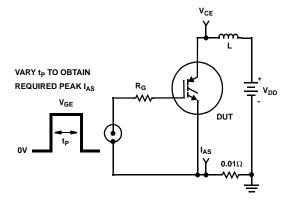


Figure 19. Unclamped Energy Test Circuit

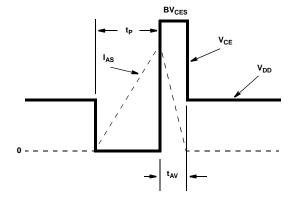


Figure 20. Unclamped Energy Waveforms

SPICE Thermal Model JUNCTION **REV 25 April 2002** ISL9V2040D3S, ISL9V2040S3S, ISL9V2040P3 CTHERM1 th 6 1.3e -2 CTHERM2 6 5 8.8e -4 CTHERM3 5 4 8.8e -3 RTHERM1 CTHERM1 CTHERM4 4 3 3.9e -1 CTHERM5 3 2 3.6e -1 CTHERM6 2 tl 1.9e -1 6 RTHERM1 th 6 1.2e -1 RTHERM2 6 5 3.2e -1 RTHERM3 5 4 1.7e -1 RTHERM2 CTHERM2 RTHERM4 4 3 1.2e -1 RTHERM5 3 2 1.3e -1 RTHERM6 2 tl 2.5e -1 5 SABER Thermal Model SABER thermal model ISL9V2040D3S, ISL9V2040P3 RTHERM3 CTHERM3 template thermal_model th tl thermal c th, tl ctherm.ctherm1 th 6 = 1.3e - 3ctherm.ctherm2 6 5 = 8.8e - 4ctherm.ctherm354 = 8.8e - 3RTHERM4 CTHERM4 ctherm.ctherm4 4 3 = 3.9e -1 ctherm.ctherm5 32 = 3.6e - 1ctherm.ctherm6 2 tl = 1.9e -1 3 rtherm.rtherm1 th 6 = 1.2e -1 rtherm.rtherm2 6 5 = 3.2e - 1rtherm.rtherm354 = 1.7e - 1RTHERM5 CTHERM5 rtherm.rtherm4 4 3 = 1.2e - 1rtherm.rtherm5 32 = 1.3e - 1rtherm.rtherm6 2 tl = 2.5e -1 2 RTHERM6 CTHERM6

CASE





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Dennicion of Terms		
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Preliminary	First Production	Datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.
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